imall

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832 Email & Skype: info@chipsmall.com Web: www.chipsmall.com Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



PTN36043 USB Type-C SuperSpeed active switch Rev. 2 — 19 February 2018

1. General description

PTN36043 is a very small, low power 2 differential channel 2 to 1 active multiplex/demultiplexer switch with integrated SuperSpeed USB 3.1 Gen 1 (also known as USB 3.0) redriver IC that can switch two differential signals to one of two locations. The active switch has optimized performance with minimized crosstalk, as required by the high-speed serial interface for USB Type-C connector. PTN36043 allows expansion of existing high-speed ports for very low power consumption.

With integrated USB 3.1 Gen 1 redriver, signal quality is enhanced by performing receive equalization on the deteriorated input signal followed by transmit de-emphasis maximizing system link performance. With its superior differential signal conditioning and enhancement capability, the device delivers significant flexibility and performance scaling for various systems with different PCB characteristics and cable channel conditions and still benefit from optimum power consumption.

PTN36043 has built-in advanced power management capability that enables significant power savings under various different USB 3.1 Gen 1 Low-power modes (U2/U3). It can detect link electrical conditions and can dynamically activate/de-activate internal circuitry and logic. The device performs these actions without host software intervention and conserves power.

PTN36043 is powered from a 1.8 V supply and is available in a small DHX2QFN18 package (2.4 mm \times 2.0 mm \times 0.35 mm) with 0.4 mm pitch.

Features and benefits 2.

- 2 bidirectional differential channel, 2 : 1 multiplex/demultiplexer switch, supports USB 3.1 Gen 1 specification (SuperSpeed only)
- Compliant to SuperSpeed USB 3.1 Gen 1 standard
- Pin out data flow matches USB Type-C connector pin assignments
- Two control pins for each channel to select optimized signal conditions
 - Receive equalization on each channel to recover from InterSymbol Interference (ISI) and high-frequency losses, with provision to choose equalization gain settings per channel
 - Transmit de-emphasis on each channel delivers pre-compensation suited to channel conditions
 - Output swing adjustment
- Integrated termination resistors provide impedance matching on both transmit and receive sides
- Automatic receiver termination detection
- Low active power: 203 mW/113 mA (typical) for VDD = 1.8 V



PTN36043

- Power-saving states:
 - 1.35 mW/0.75 mA (typical) when in U2/U3 states
 - ◆ 0.81 mW/0.45 mA (typical) when no connection detected
- Excellent differential and common return loss performance
 - ◆ 14 dB differential and 15 dB common-mode return loss for 10 MHz to 1250 MHz
- Flow-through pinout to ease PCB layout and minimize crosstalk effects
- Power supply: VDD = 1.8 V (typical)
- Compliant with JESD 78 Class II latch up test standard
- Very thin DHX2QFN18 package: 2.4 mm x 2.0 mm x 0.35 mm, 0.4 mm pitch
- ESD protection exceeds 7000 V HBM per JDS-001-2012 and 1000 V CDM per JESD22-C101
- Latch-up testing is done to JEDEC Standard JESD78 which exceeds 100 mA
- Operating temperature range: -40°C to +85°C

3. Applications

- USB 3.1 Gen 1 application for USB Type-C connectors
- Smart Phones, Tablets/Mobile Devices
- Desktop/Notebook Computers
- Docking Stations
- USB 3.1 Gen 1 Peripherals such as flat panel display, consumer/storage devices, printers or USB 3.1 Gen 1 capable hubs/repeaters

4. Ordering information

Table 1.Ordering information

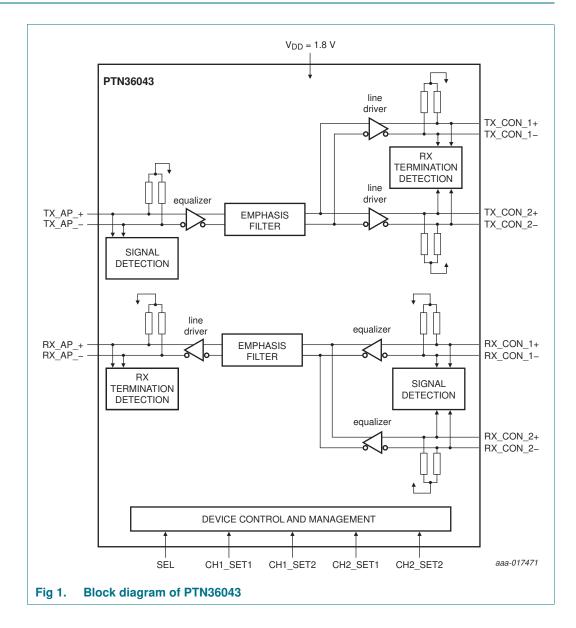
Type number	Topside	Package		
	marking	Name	Description	Version
PTN36043BX	43		plastic dual in-line compatible thermal enhanced extremely thin quad flat package; no leads; 18 terminals; body 2.4 mm \times 2.0 mm \times 0.35 mm	SOT1442-1

4.1 Ordering options

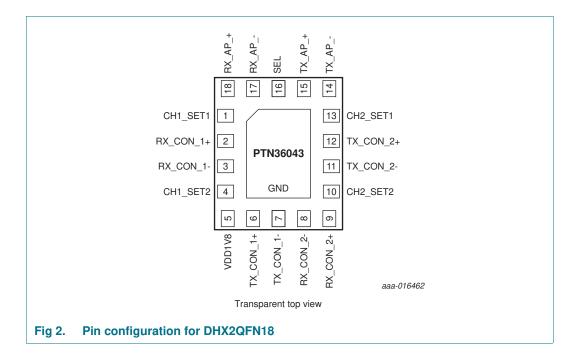
Table 2.Ordering options

71	Orderable part number	Package	3 1 1	Minimum order quantity	Temperature
PTN36043BX	PTN36043BXY	DHX2QFN18	REEL 13" Q1/T1 *STANDARD MARK SMD DP	10000	$T_{amb} = -40 \ ^{\circ}C \ to \ +85 \ ^{\circ}C$

5. Block diagram



6. Pinning information



6.1 Pinning

6.2 Pin description

Symbol	Pin	Туре	Description				
RX_AP_+	18	Output	USB 3.1 Gen 1 differential output signals of the RX				
RX_AP	17		path to application processor				
TX_AP_+	15	Input	USB 3.1 Gen 1 differential input signals of the TX				
TX_AP	14		path from application processor				
TX_CON_1+	6	Output	USB 3.1 Gen 1 differential output signals of the TX				
TX_CON_1-	7		path to connector side port 1				
RX_CON_1+	2	Input	USB 3.1 Gen 1 differential input signals of the RX				
RX_CON_1-	3		path from connector side port 1				
TX_CON_2+	12	Output	USB 3.1 Gen 1 differential output signals of the TX				
TX_CON_2-	11		path to connector side port 2				
RX_CON_2+	9	Input	USB 3.1 Gen 1 differential input signals of the RX				
RX_CON_2-	8		path from connector side port 2				

Symbol	Pin	Туре	Description
SEL	16	input	Output selection control
			When SEL=0, RX_AP_ \pm /TX_AP_ \pm are connected to RX_CON_2 \pm /TX_CON_2 \pm , and RX_CON_1 \pm /TX_CON_1 \pm are connected to VDD thru low ohmic resistor (50 Ω).
			When SEL=1, RX_AP_ \pm /TX_AP_ \pm are connected to RX_CON_1 \pm /TX_CON_1 \pm , and RX_CON_2 \pm /TX_CON_2 \pm are connected to VDD thru low ohmic resistor (50 Ω).
CH1_SET1	1	Ternary	OS/DE/EQ control pins for channel facing the
CH1_SET2	4	input	application processor side
CH2_SET1	13	Ternary	OS/DE/EQ control pins for channel facing the
CH2_SET2	10	input	connector side
VDD1V8	5	Power	Power supply (1.8 V typical)
GND	Center Pad	Power	Ground. Center pad must be connected to GND plane for both electrical grounding and thermal relief purposes.

Table 3. Pin description ...continued

7. Functional description

Refer to Figure 1 "Block diagram of PTN36043".

PTN36043 is a high speed 2 to 1 active switch with integrated SuperSpeed USB 3.1 Gen 1 redriver meant to be used for signal integrity enhancement on various platforms - smart phone, tablet, notebook, hub, A/V display and peripheral devices, for example. With its high fidelity differential signal conditioning capability and wide configurability, this device is flexible and versatile enough for use under a variety of system environments.

The following sections describe the individual block functions and capabilities of the device in more detail.

7.1 Receive equalization, transmitter de-emphasis and output swing level controls

On the high-speed signal path, the device performs receive equalization (EQ) and transmitter de-emphasis (DE) and output swing control (OS). In addition, the device provides flat frequency gain by boosting output signal. Both flat and frequency selective gains prepare the system to cover up to losses further down the link.

<u>Table 4</u> lists DE/OS/EQ configuration options of the channel toward application processor side.

CH1_SET1	CH1_SET2	RX_AP_± De-emphasis	RX_AP_± Output Swing	TX_AP_± Equalizer
LOW	LOW	–3.9 dB	1100 mV	3.0 dB
	OPEN	–3.5 dB	900 mV	3.0 dB
	HIGH	0 dB	1100 mV	3.0 dB
OPEN	LOW	0 dB	900 mV	3.0 dB
	OPEN	–3.9 dB	1100 mV	0 dB
	HIGH	–3.5 dB	900 mV	0 dB
HIGH	LOW	0 dB	1100 mV	0 dB
	OPEN	0 dB	900 mV	0 dB
	HIGH	–5.3 dB	1100 mV	6.0 dB

Table 4. Application Processor side DE/OS/EQ configuration options

Table 5 lists DE/OS/EQ configuration options of the channel toward connector side.

CH2_SET1	CH2_SET2	TX_CON_1± TX_CON_2± De-emphasis	TX_CON_1± TX_CON_2± Output Swing	RX_CON_1± RX_CON_2± Equalizer				
LOW	LOW	–5.3 dB	1100 mV	0 dB				
	OPEN	–3.9 dB	1100 mV	0 dB				
	HIGH	–3.5 dB	900 mV	0 dB				
OPEN	LOW	–5.1 dB	900 mV	0 dB				
	OPEN	–3.9 dB	1100 mV	6.0 dB				
	HIGH	–3.5 dB	900 mV	6.0 dB				
HIGH	LOW	–5.3 dB	1100 mV	6.0 dB				
	OPEN	–5.1 dB	900 mV	6.0 dB				
	HIGH	–5.3 dB	1100 mV	9.0 dB				

 Table 5.
 Connector side DE/OS/EQ configuration options

7.2 Device states and power management

PTN36043 has implemented an advanced power management scheme that operates in tune with USB 3.1 Gen 1 bus electrical condition. Although the device does not decode USB power management commands (related to USB 3.1 Gen 1 U1/U2/U3 transitions) exchanged between USB 3.1 Gen 1 host and peripheral/device, it relies on bus electrical conditions and SEL pin setting to decide to be in one of the following states:

- Active state wherein device is fully operational, USB data is transported on either port 1 or port 2 in Figure 1. In this state, USB connection exists and the Receive Termination indication remains active. But there is no need for Receive Termination detection.
- **Power-saving state** wherein either port 1 or port 2 is kept enabled. In this state, squelching, detection and/or Receive termination detection circuitry are active. Based on USB connection, there are two possibilities:
 - No USB connection.
 - A USB connection exists and the link is in USB 3.1 Gen 1 U2/U3 mode.
- Off state when PTN36043 is not being powered (i.e., VDD1V8 = 0 V), special steps should be done to prevent back-current issues on control pins such SEL or CH1/2_SET1/2 pins when these pins' states are not low. These pins can be controlled through two different ways.
 - pull-up/pull-down resistors make sure these pull-up resistors' VDD is the same power source as to power PTN36043. When power to PTN36043 is off, power to these pull-up resistors will be off as well.
 - external processor's GPIO if PTN36043 is turned off when the external processor's power stays on, processor should configure these GPIOs connected to these control pins as output low (< 0.4 V) or tri-state mode (configure GPIOs as input mode). This will make sure no current will be flowing into PTN36043 through these control pins.

7.3 SEL input pin

PTN36043 is designed with 1:2 high speed de-multiplexer configuration. TX_AP_ \pm and RX_AP_ \pm can be connected to either TX_CON_1 \pm and RX_CON_1 \pm , or TX_CON_2 \pm and RX_CON_2 \pm by changing the SEL input state.

Table 6.	SEL input setting
SEL	Function
0	TX_CON_2± and RX_CON_2± are connected to TX_AP_± and RX_AP_±
	TX_CON_1± and RX_CON_1± are connected to VDD thru low ohmic resistor (50 Ω).
1	TX_CON_1± and RX_CON_1± are connected to TX_AP_± and RX_AP_±
	TX_CON_2± and RX_CON_2± are connected to VDD thru low ohmic resistor (50 Ω).

8. Application guideline for Control of CHx_SETx and SEL input pins

PTN36043 implements ternary control IO logic on CHx_SETx and SEL control pins to detect HIGH (connected to VDD), LOW (connected to GND) or left unconnected condition (OPEN).

For all control pins except SEL, all 3 pin conditions are applicable. If the SEL pin is left unconnected (OPEN), the internal logic treats it as LOW.

To minimize the current consumption of IO circuitry on SEL pin, it is recommended this pin be driven from 1.8 V capable push-pull IO. If 1.8 V push-pull IO is not available in the application, the SEL pin can be driven from an open drain grounded NMOS GPIO with external pull-up resistor to the 1.8 V supply of PTN36043. The recommended value of the external pull-up resistor is 30 k Ω .

9. Limiting values

Table 7. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DD(1V8)}	supply voltage (1.8 V)	<u>[1]</u>	-0.3	+2.2	V
VI	input voltage	<u>[1]</u>	-0.3	+2.2	V
T _{stg}	storage temperature		-65	+150	°C
V _{ESD}	electrostatic discharge voltage	HBM [2]	-	7000	V
		CDM [3]	-	1000	V

[1] All voltage values (except differential voltages) are with respect to network ground terminal.

[2] Human Body Model: ANSI/EOS/ESD-S5.1-1994, standard for ESD sensitivity testing, Human Body Model - Component level; Electrostatic Discharge Association, Rome, NY, USA.

[3] Charged Device Model: ANSI/EOS/ESD-S5.3-1-1999, standard for ESD sensitivity testing, Charged Device Model - Component level; Electrostatic Discharge Association, Rome, NY, USA.

10. Recommended operating conditions

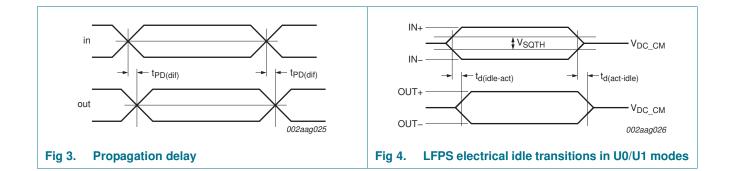
Table 8. Operating conditions

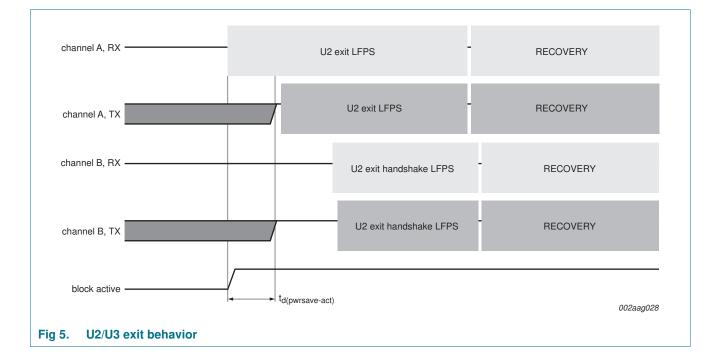
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DD(1V8)}	supply voltage (1.8 V)	1.8 V supply option	1.7	1.8	1.9	V
VI	input voltage	CMOS inputs	-0.3	V _{DD(1V8)}	+2.2	V
		differential pairs	-0.3	-	+2.2	V
T _{amb}	ambient temperature	operating in free air	-40	-	+85	°C

11. Characteristics

11.1 Device characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
t _{startup}	start-up time	between supply voltage within operating range (90 % of V _{DD}) until automatic receiver termination detection	-	-	6	ms
t _{rcfg1}	setting reconfiguration time	any configuration pin change (from one setting to another setting) to specified operating characteristics; device is supplied with valid supply voltage	-	-	3	ms
t _{rcfg2}	port reconfiguration time	Switching from one port to the other port (i.e., Port 1 to Port 2 or vice versa) until automatic receiver detection; device is supplied with valid supply voltage	-	-	7	ms
t _{PD(dif)}	differential propagation delay	between 50 % level at input and output; see <u>Figure 3</u>	-	-	0.5	ns
t _{idle}	idle time	default wait time to wait before getting into Power-saving state	-	300	400	ms
t _{d(pwrsave-act)}	delay time from power-save to active	time for exiting from Power-saving state and get into Active state; see $\frac{\text{Figure 5}}{5}$	-	-	115	μS
t _{d(act-idle)}	delay time from active to idle	reaction time for squelch detection circuit; see Figure 4	-	9	14	ns
t _{d(idle-act)}	delay time from idle to active	reaction time for squelch detection circuit; see Figure 4	-	5	11	ns
DDNEXT	Differential near-end crosstalk between TX and RX signal pairs within the same port	f < 2.5 GHz	-	-50	-	dB
R _{th(j-a)}	thermal resistance from junction to ambient	JEDEC still air test environment; value is based on simulation under JEDEC still air test environment with 2S2P(4L) JEDEC PCB	-	96	-	°C/W
Ψ _{jt}	junction to top of case thermal characterization parameter	to case top; at ambient temperature of 85 °C; value is based on simulation under JEDEC still air test environment with 2S2P(4L) JEDEC PCB	-	1.0	-	°C/W
I _{DD}	supply current	Active state				
		OS = 1100 mV/DE = -3.9 dB for both AP side and CON side	-	113	-	mA
		$\label{eq:states} \begin{array}{l} \text{OS} = 900 \text{ mV/DE} = -3.5 \text{ dB for AP side,} \\ \text{OS} = 1100 \text{ mV/DE} = -3.9 \text{ dB for CON side} \end{array}$	-	108	-	mA
		$\label{eq:oscillator} \begin{array}{l} \text{OS} = 900 \text{ mV/DE} = 0 \text{ dB for AP side}, \\ \text{OS} = 1100 \text{ mV/DE} = -3.9 \text{ dB for CON side} \end{array}$	-	103	6 3 7 0.5 400 115 14	mA
		U2/U3 Power-saving state	-	0.75		mA
		no USB connection state	-	0.45		mA





11.2 Receiver AC/DC characteristics

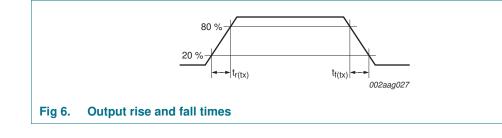
Table 10. Receiver AC/DC characteristics	Table 10.
--	-----------

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Z _{RX_DC}	receiver DC common-mode impedance		18	-	30	Ω
Z _{RX_DIFF_DC}	DC differential impedance	RX pair	72	-	120	Ω
Z _{RX_HIGH_IMP}	common-mode input impedance	DC common-mode input impedance when output of redriver is not terminated	25	-	-	kΩ
V _{RX(diff)(p-p)}	peak-to-peak differential receiver voltage		100	-	1200	mV
V _{RX_DC_CM}	RX DC common mode voltage		-	1.8	-	V
V _{RX_CM_AC_P}	RX AC common-mode voltage	peak	-	-	150	mV
V _{th(i)}	signal detector input threshold voltage	differential peak-to-peak value	75	-	150	mV
RL _{DD11,RX}	RX differential mode return loss	10 MHz to 1250 MHz	12	14	-	dB
		1250 MHz to 2500 MHz	7	8.5	-	dB
		2500 MHz to 3000 MHz	6	7.5	-	dB
RL _{CC11,RX}	RX common mode return loss	10 MHz to 1250 MHz	12	15	-	dB
		1250 MHz to 2500 MHz	8	10	-	dB
		2500 MHz to 3000 MHz	7	9	-	dB

11.3 Transmitter AC/DC characteristics

Table 11. Transmitter AC/DC characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Z _{TX_DC}	transmitter DC common-mode impedance		18	-	30	Ω
Z _{TX_DIFF_DC}	DC differential impedance		72	-	120	Ω
V _{TX_DIFFp-p}	differential peak-to-peak	R _L = 100 Ω				
	output voltage	OS = 900 mV	800	900	1000	mV
		OS = 1100 mV	1000	1100	1200	mV
V _{TX_DC_CM}	transmitter DC common-mode voltage		-	1.3	V _{DD(1V8)}	V
VTX_CM_ACpp_ACTIV	TX AC common-mode peak-to-peak output voltage (active state)	device input fed with differential signal	-	-	100	mV
VTX_IDL_DIFF_ACpp	electrical idle differential peak-to-peak output voltage	when link is in electrical idle	-	-	10	mV
t _{W(deemp)} TX	transmitter de-emphasis pulse width		160	180	200	ps
V _{TX_RCV_DETECT}	voltage change allowed during receiver detection	positive voltage swing to sense the receiver termination detection	-	0.5 × V _{TX_DIFFp-p}	600	mV
R _{TX_RCV_DETECT}	TX receiver termination detect charging resistance	output resistor of the transmitter when it does RX detection	-	3.1	-	kΩ
t _{r(tx)}	transmit rise time	measured using 20 % and 80 % levels; see <u>Figure 6</u>	40	55	75	ps
t _{f(tx)}	transmit fall time	measured using 20 % and 80 % levels; see Figure 6	40	55	75	ps
t _{(r-f)tx}	difference between transmit rise and fall time	measured using 20 % and 80 % levels	-	-	20	ps
RL _{DD11,TX}	TX differential mode return	10 MHz to 1250 MHz	12	13.5	-	dB
	loss	1250 MHz to 2500 MHz	6.5	8	-	dB
		2500 MHz to 3000 MHz	5	6.5	-	dB
RL _{CC11,TX}	TX common mode return loss	10 MHz to 1250 MHz	12	14	-	dB
		1250 MHz to 2500 MHz	8	10	-	dB
		2500 MHz to 3000 MHz	9	10	-	dB



11.4 Ternary control inputs

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{IH}	HIGH-level input voltage	Trigger level of the Schmitt Trigger buffer when input is going from LOW to HIGH	$0.70 \times V_{DD}$	V _{DD}	V _{DD} + 0.3	V
V _{IL}	LOW-level input voltage	Trigger level of the Schmitt Trigger buffer when input is going from HIGH to LOW	-0.3	0	$0.30 \times V_{DD}$	V
R _{pu(ext)}			0	-	30	kΩ
R _{pd(ext)}	external pull-down resistor	connected between setting pin and GND; for detection of LOW condition	0	-	30	kΩ
Z _{ext(OPEN)}	external impedance	for detection of OPEN condition	250	-	-	kΩ
I _{IL}	LOW-level input current	setting pin is driven LOW by external GPIO	-45	-	-	μA
I _{IH}	HIGH-level input current	setting pin is driven HIGH (to 1.8 V) by external GPIO	-	-	+45	μA
I _{Lext(OPEN)}	external leakage current	ternal leakage current of external GPIO; for reliable detection of OPEN condition		-	+6	μA
C _{L(ext)}	external load on setting pin; for reliable detection of OPEN condition		-	-	150	pF
R _{pu(int)}	internal pull-up resistance	for detection of Ternary setting	-	50	-	kΩ
R _{pd(int)}	internal pull-down resistance	for detection of Ternary setting	-	50	-	kΩ

Table 12. Ternary control inputs CHx_SETx characteristics^[1]

[1] See <u>Section 8</u> for application guidelines for the Ternary control pins.

Table 13. Ternary control input SEL characteristics^[1]

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{IH}	HIGH-level input voltage	Trigger level of the Schmitt Trigger buffer when input is going from LOW to HIGH	$0.70 \times V_{DD}$	V _{DD}	V _{DD} + 0.3	V
V _{IL}	LOW-level input voltage	Trigger level of the Schmitt Trigger buffer when input is going from HIGH to LOW	-0.3	0	$0.30 \times V_{DD}$	V
R _{pu(ext)}	external pull-up resistor	connected between VDD1V8 and setting pin; for detection of HIGH condition	0	-	30	kΩ
R _{pd(ext)}	external pull-down resistor	connected between setting pin and GND; for detection of LOW condition	0	-	30	kΩ
Z _{ext(OPEN)}	external impedance	for detection of OPEN condition and will be interpreted as LOW condition	250	-	-	kΩ
I _{IL}	LOW-level input current	setting pin is driven LOW by external GPIO	-45	-	-	μA

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{IH}	HIGH-level input current	setting pin is driven HIGH (to 1.8 V) by external GPIO	-	-	+45	μA
C _{L(ext)}	external load capacitance	on setting pin; for reliable detection of OPEN condition	-	-	150	pF
R _{pu(int)}	internal pull-up resistance	for detection of Ternary setting	-	50	-	kΩ
R _{pd(int)}	internal pull-down resistance	for detection of Ternary setting	-	50	-	kΩ

Table 13. Ternary control input SEL characteristics^[1] ...continued

[1] See <u>Section 8</u> for application guidelines for the Ternary control pins.

12. Package outline

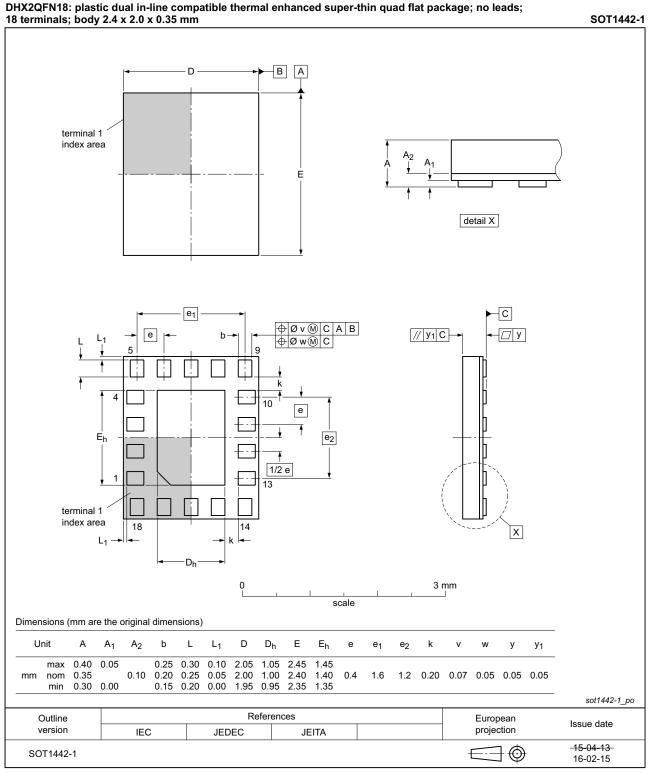


Fig 7. Package outline SOT1442-1 (DHX2QFN18)

13. Packing information

- 13.1 SOT1442-1 (DHXQFN18); Reel dry pack, SMD, 13" Q1/T1 standard product orientation; Orderable part number ending ,518 or Y; Ordering code (12NC) ending 518
- 13.1.1 Packing method

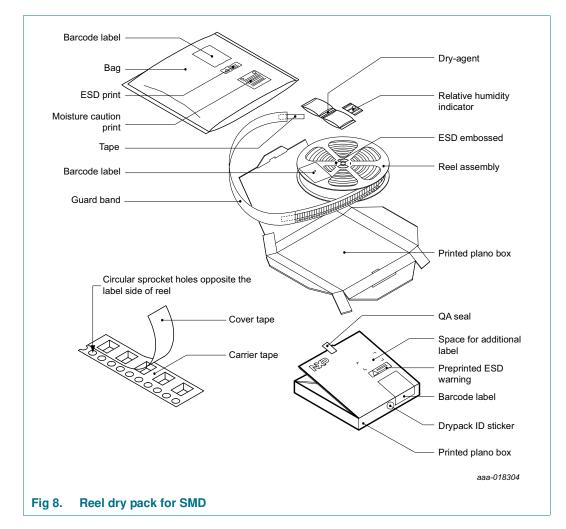


Table 14. Dimensions and quantities

			Outer box dimensions $I \times w \times h$ (mm)
330 × 8	10000	1	$342\times 338\times 39$

[1] d = reel diameter; w = tape width.

Packing quantity dependent on specific product type.
 View ordering and availability details at NXP order portal, or contact your local NXP representative.

13.1.1.1 Product orientation



13.1.1.2 Carrier tape dimensions

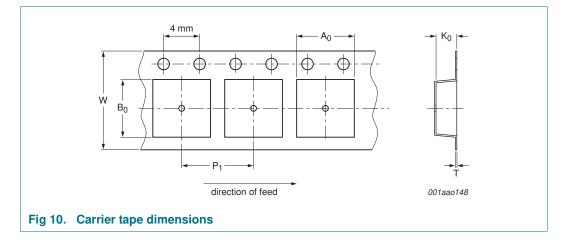


Table 15.Carrier tape dimensionsIn accordance with IEC 60286-3.

 A_0 (mm) B_0 (mm) K_0 (mm)T (mm) P_1 (mm)W (mm) 2.25 ± 0.1 2.65 ± 0.1 0.53 ± 0.05 0.25 ± 0.03 4.0 ± 0.1 8.0 + 0.3 / - 0.1

13.1.1.3 Reel dimensions

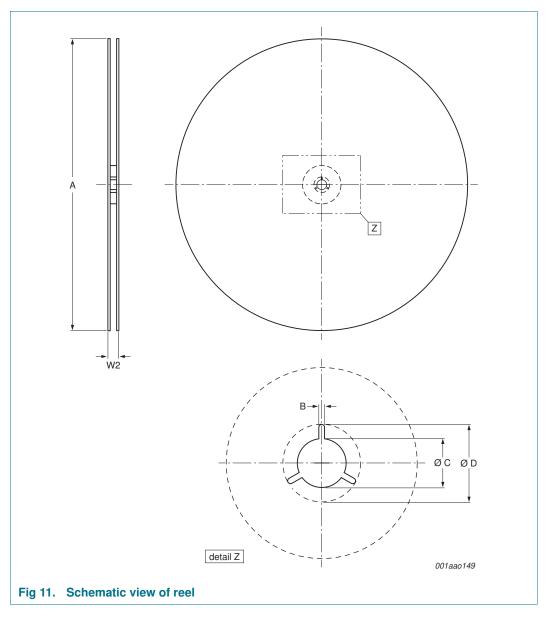


Table 16. Reel dimensions

In accordance with IEC 60286-3.

A [nom]	W2 [max]	B [min]	C [min]	D [min]
(mm)	(mm)	(mm)	(mm)	(mm)
330	14.4	1.5	12.8	20.2

PTN36043

13.1.1.4 Barcode label

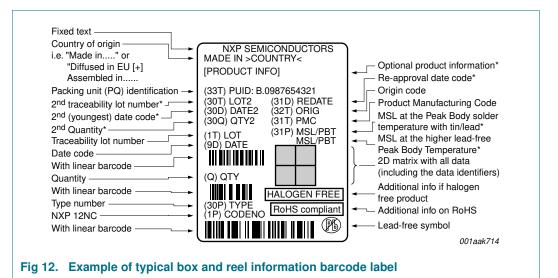


Table 17. Barcode label dimensions

	Reel barcode label I × w (mm)
100×75	100 × 75

14. Soldering of SMD packages

This text provides a very brief insight into a complex technology. A more in-depth account of soldering ICs can be found in Application Note *AN10365 "Surface mount reflow soldering description"*.

14.1 Introduction to soldering

Soldering is one of the most common methods through which packages are attached to Printed Circuit Boards (PCBs), to form electrical circuits. The soldered joint provides both the mechanical and the electrical connection. There is no single soldering method that is ideal for all IC packages. Wave soldering is often preferred when through-hole and Surface Mount Devices (SMDs) are mixed on one printed wiring board; however, it is not suitable for fine pitch SMDs. Reflow soldering is ideal for the small pitches and high densities that come with increased miniaturization.

14.2 Wave and reflow soldering

Wave soldering is a joining technology in which the joints are made by solder coming from a standing wave of liquid solder. The wave soldering process is suitable for the following:

- Through-hole components
- Leaded or leadless SMDs, which are glued to the surface of the printed circuit board

Not all SMDs can be wave soldered. Packages with solder balls, and some leadless packages which have solder lands underneath the body, cannot be wave soldered. Also, leaded SMDs with leads having a pitch smaller than ~0.6 mm cannot be wave soldered, due to an increased probability of bridging.

The reflow soldering process involves applying solder paste to a board, followed by component placement and exposure to a temperature profile. Leaded packages, packages with solder balls, and leadless packages are all reflow solderable.

Key characteristics in both wave and reflow soldering are:

- · Board specifications, including the board finish, solder masks and vias
- · Package footprints, including solder thieves and orientation
- The moisture sensitivity level of the packages
- · Package placement
- · Inspection and repair
- Lead-free soldering versus SnPb soldering

14.3 Wave soldering

Key characteristics in wave soldering are:

- Process issues, such as application of adhesive and flux, clinching of leads, board transport, the solder wave parameters, and the time during which components are exposed to the wave
- · Solder bath specifications, including temperature and impurities

14.4 Reflow soldering

Key characteristics in reflow soldering are:

- Lead-free versus SnPb soldering; note that a lead-free reflow process usually leads to higher minimum peak temperatures (see Figure 13) than a SnPb process, thus reducing the process window
- Solder paste printing issues including smearing, release, and adjusting the process window for a mix of large and small components on one board
- Reflow temperature profile; this profile includes preheat, reflow (in which the board is heated to the peak temperature) and cooling down. It is imperative that the peak temperature is high enough for the solder to make reliable solder joints (a solder paste characteristic). In addition, the peak temperature must be low enough that the packages and/or boards are not damaged. The peak temperature of the package depends on package thickness and volume and is classified in accordance with Table 18 and 19

Package thickness (mm)	Package reflow temperature (°C)		
	Volume (mm ³)		
	< 350	≥ 350	
< 2.5	235	220	
≥ 2.5	220	220	

Table 18. SnPb eutectic process (from J-STD-020D)

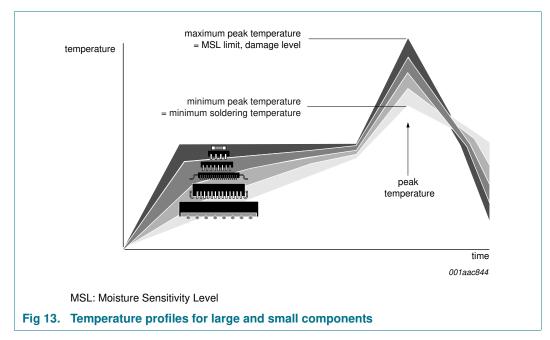
Table 19. Lead-free process (from J-STD-020D)

Package thickness (mm)	Package reflow temperature (°C)			
	Volume (mm ³)			
	< 350	> 2000		
< 1.6	260	260	260	
1.6 to 2.5	260	250	245	
> 2.5	250	245	245	

Moisture sensitivity precautions, as indicated on the packing, must be respected at all times.

Studies have shown that small packages reach higher temperatures during reflow soldering, see Figure 13.

PTN36043



For further information on temperature profiles, refer to Application Note *AN10365 "Surface mount reflow soldering description"*.

15. Soldering

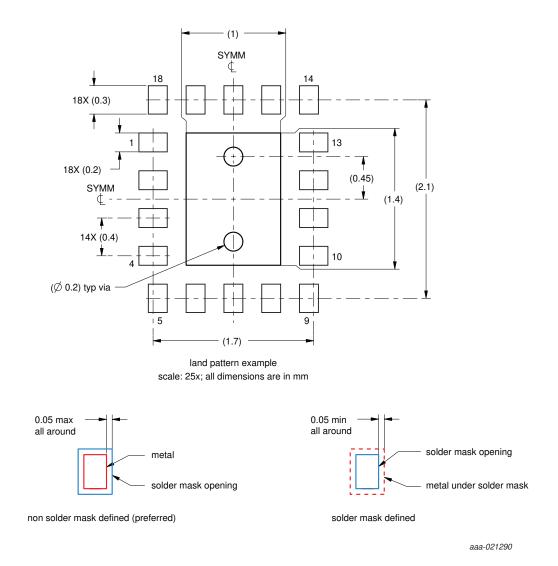
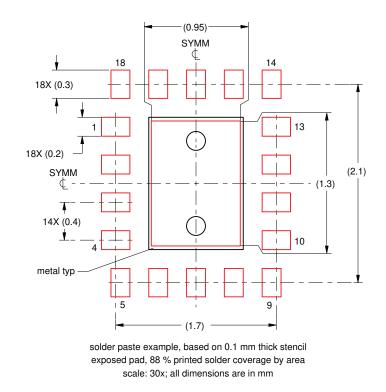


Fig 14. PCB footprint for SOT1442-1 (DHX2QFN18); reflow soldering

PTN36043



aaa-021333

Fig 15. Solder paste example